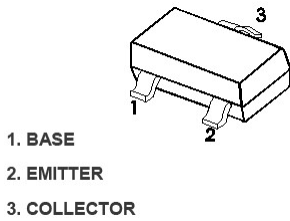


SOT-23**SOT-23 贴片塑封三极管**
SOT-23 Plastic-Encapsulate Transistors**Marking: G1****特征 Features**

- 与 MMBT5401 配对; Complementary to MMBT5401
- 最大功率耗散 300mW; Power Dissipation of 300mW
- 高稳定性和可靠性。High Stability and High Reliability

机械数据 Mechanical Data

- 封装: SOT-23 封装 SOT-23 Small Outline Plastic Package
- 环氧树脂 UL 易燃等级 Epoxy UL: 94V-0
- 安装位置: 任意 Mounting Position: Any

极限值和温度特性(TA = 25°C 除非另有规定)

Maximum Ratings & Thermal Characteristics (Ratings at 25°C ambient temperature unless otherwise specified.)

参数 Parameters	符号 Symbol	数值 Value	单位 Unit
Collector-Base Voltage	V _{CBO}	180	V
Collector-Emitter Voltage	V _{CEO}	160	V
Emitter -Base Voltage	V _{EBO}	6	V
Collector Current-Continuous	I _C	600	mA
Collector Power Dissipation	P _C	300	mW
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55-+150	°C
Thermal resistance From junction to ambient	R _{θJA}	416	°C/W

电特性 (TA = 25°C 除非另有规定)

Electrical Characteristics (Ratings at 25°C ambient temperature unless otherwise specified.)

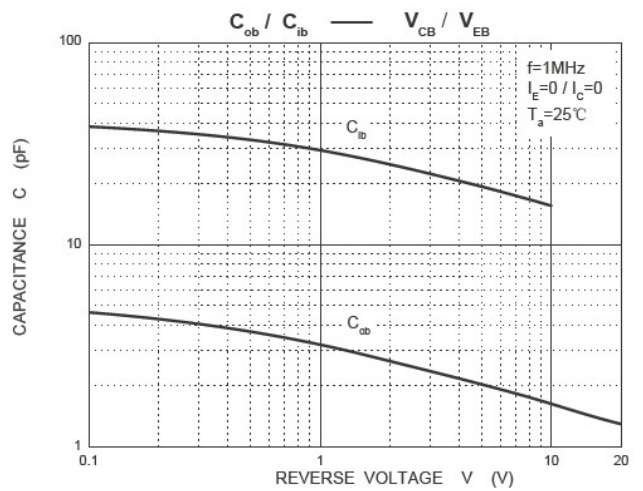
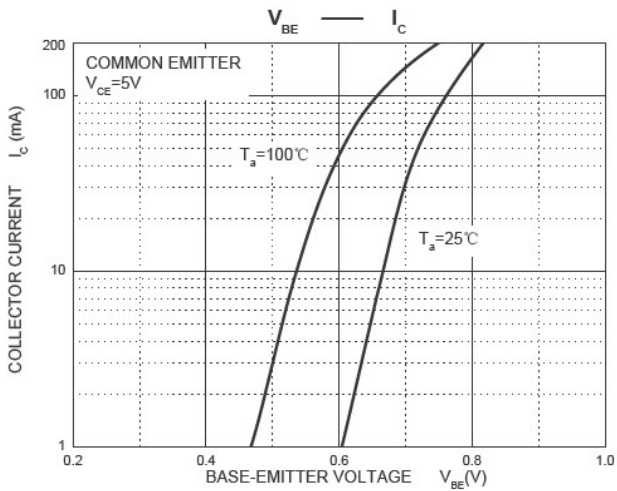
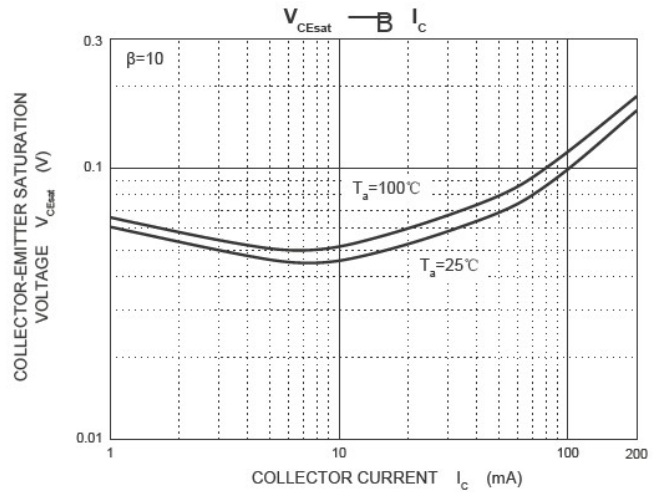
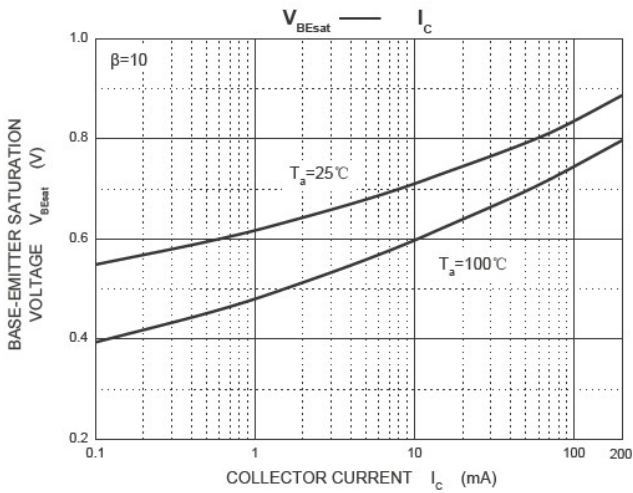
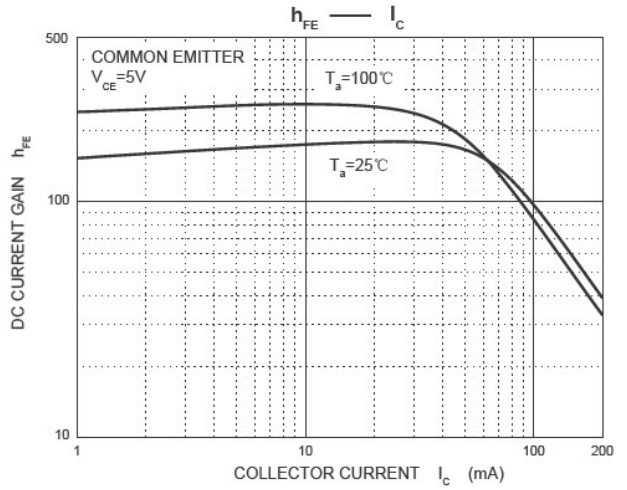
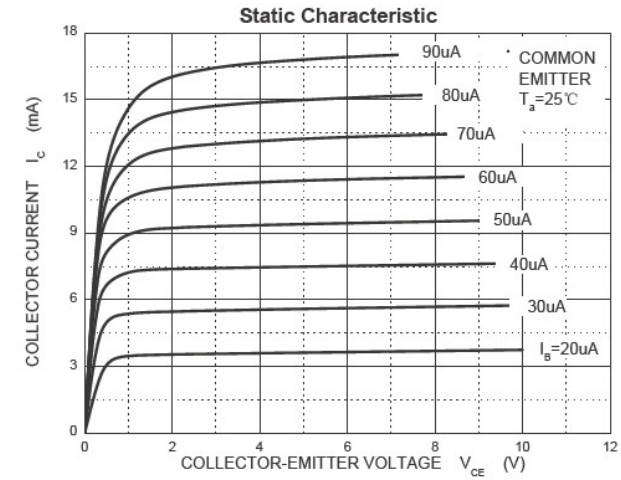
参数 Parameter	符号 Symbols	测试条件 Test Condition	界限 Limits		单位 Unit
			Min	Max	
Collector-base breakdown voltage	V(BR)CBO	I _C =100μA, I _E =0	180		V
Collector-emitter breakdown voltage	V(BR)CEO *	I _C =1mA, I _B =0	160		V
Emitter-base breakdown voltage	V(BR)EBO	I _E =10μA, I _C =0	6		V
Collector cut-off current	I _{CBO}	V _{CB} =120V, I _E =0		50	nA
Emitter cut-off current	I _{EBO}	V _{EB} =4V, I _C =0		50	nA
DC current gain	hFE(1) *	V _{CE} =5V, I _C =1mA	80		
	hFE(2) *	V _{CE} =5V, I _C =10mA	100	300	
	hFE(3) *	V _{CE} =5V, I _C =50mA	30		
Collector-emitter saturation voltage	V _{CE(sat)1} *	I _C =10mA, I _B =1mA		0.15	V
	V _{CE(sat)2} *	I _C =50mA, I _B =5mA		0.20	V
Base -emitter saturation voltage	V _{BE(sat)1} *	I _C =10mA, I _B =1mA		1.00	V
	V _{BE(sat)2} *	I _C =50mA, I _B =5mA		1.00	V
Transition frequency	f _T	V _{CE} =10V, I _C =10mA, f=100MHz	100	300	MHz
Collector output capacitance	C _{ob}	V _{CB} =10V, I _E =0, f=1MHz		6	pF

*Pulse test: pulse width ≤ 300us, duty cycle ≤ 2.0%

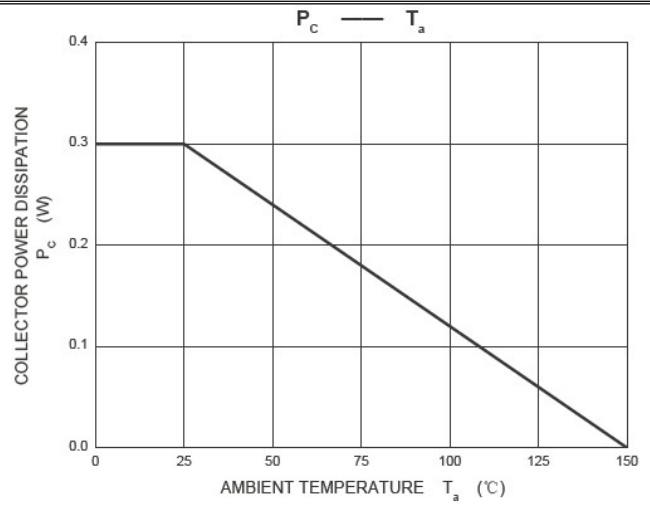
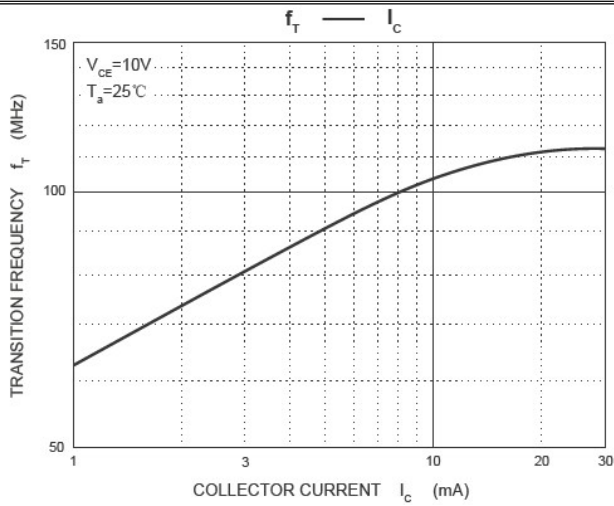
CLASSIFICATION OF hFE(2)

HFE	100-300	
RANK	L	H
RANGE	100-200	200-300

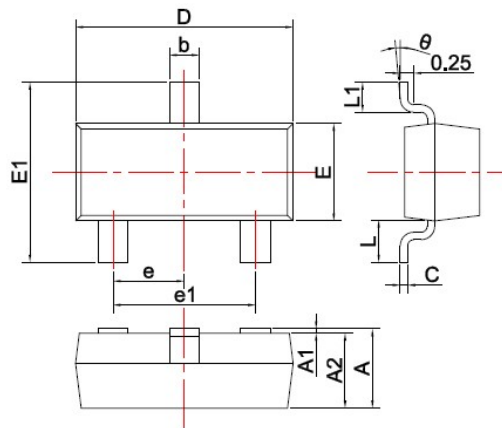
Typical characteristics



MMB5551



SOT-23 PACKAGE OUTLINE Plastic surface mounted package

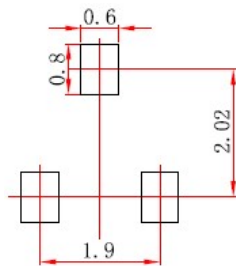


SYMBOL	DIMENSIONS	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0 $^\circ$	8 $^\circ$

Unit: mm

焊盘设计参考 Precautions: PCB Design

Recommended land dimensions for SOT-23 diode. Electrode patterns for PCBs



- Note:
1. Controlling dimension: In millimeters.
 2. General tolerance: ± 0.05 mm.
 3. The pad layout is for reference purposes only.

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for [Bipolar Transistors - BJT category](#):

Click to view products by [ZRE manufacturer](#):

Other Similar products are found below :

[619691C](#) [MCH4017-TL-H](#) [MMBT-2369-TR](#) [BC546/116](#) [BC557/116](#) [BSW67A](#) [NJVMJD148T4G](#) [NTE123AP-10](#) [NTE153MCP](#) [NTE16](#)
[NTE195A](#) [NTE92](#) [C4460](#) [2N4401-A](#) [2N6728](#) [2SA1419T-TD-H](#) [2SA2126-E](#) [2SB1204S-TL-E](#) [2SC2712S-GR,LF](#) [2SC4731T-AY](#)
[2SC5488A-TL-H](#) [2SD2150T100R](#) [SP000011176](#) [FJPF5304DTU](#) [2N2907A](#) [2N3904-NS](#) [2N5769](#) [2SB1324-TD-E](#) [2SC2412KT146S](#)
[2SC3332T](#) [2SC3902S](#) [2SC5231C8-TL-E](#) [2SD1685F](#) [2SD1816S-TL-E](#) [CPH6501-TL-E](#) [MCH4021-TL-E](#) [MJE340](#) [US6T6TR](#) [NJL0281DG](#)
[732314D](#) [CPH3121-TL-E](#) [CPH6021-TL-H](#) [873787E](#) [IMZ2AT108](#) [UMX21NTR](#) [MCH6102-TL-E](#) [NJL0302DG](#) [2N3583](#) [30A02MH-TL-E](#)
[NSV40301MZ4T1G](#)